



Description

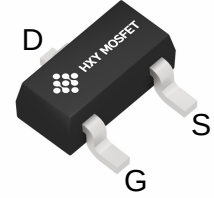
The HXY3400BMI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

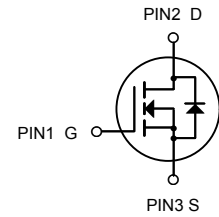
$V_{DS} = 30V, I_D = 5.8A$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 38m\Omega @ V_{GS}=4.5V$

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



SOT-23-3L



N-Channel MOSFET

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3400BMI	SOT23-3L	X01V	3000PCS

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	5.8	A
I_{DM}	Drain Current-Pulsed (Note 1)	20.4	A
P_D	Maximum Power Dissipation	1.4	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	89	$^{\circ}C/W$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	-	1.3	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =4A	-	24	28	mΩ
		V _{GS} =4.5V, I _D =3A	-	27	38	
		V _{GS} =2.5V, I _D =3A	-	36	54	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	507	-	pF
C _{oss}	Output Capacitance		-	52	-	pF
C _{rss}	Reverse Transfer Capacitance		-	43	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =5A, V _{GS} =4.5V	-	9.1	-	nC
Q _{gs}	Gate-Source Charge		-	2.1	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	2.8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, R _{GEN} =3Ω, R _L =2.8Ω, V _{GS} =10V	-	3	-	ns
t _r	Turn-on Rise Time		-	2.8	-	ns
t _{d(off)}	Turn-off Delay Time		-	25	-	ns
t _f	Turn-off Fall Time		-	4	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =5A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

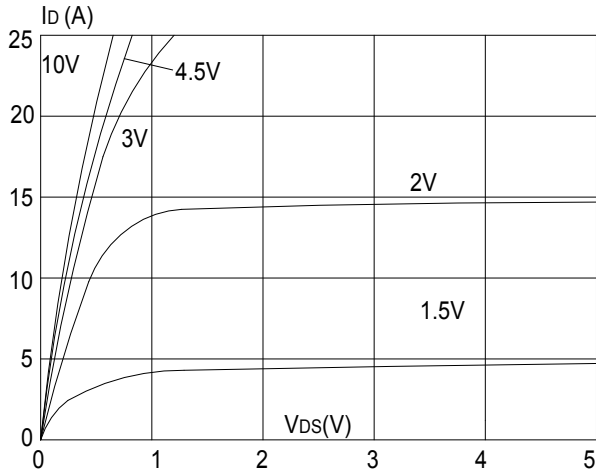


Figure 2: Typical Transfer Characteristics

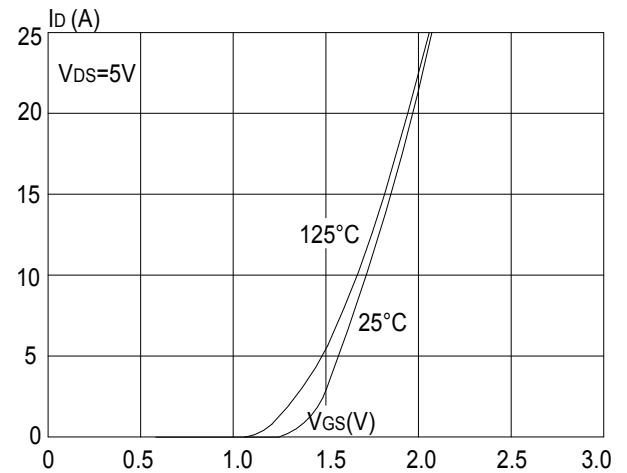


Figure 3: On-resistance vs. Drain Current

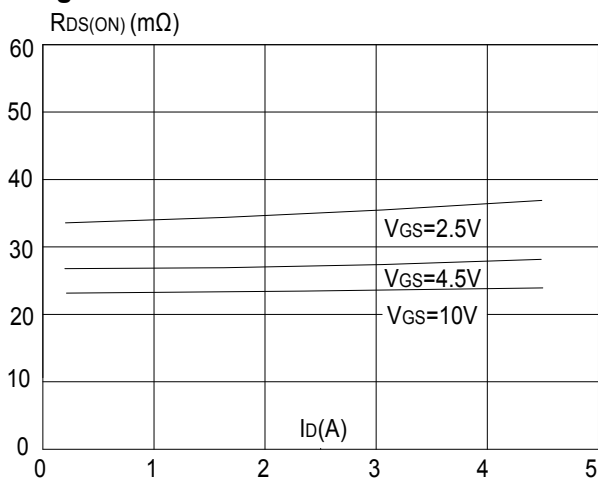


Figure 4: Body Diode Characteristics

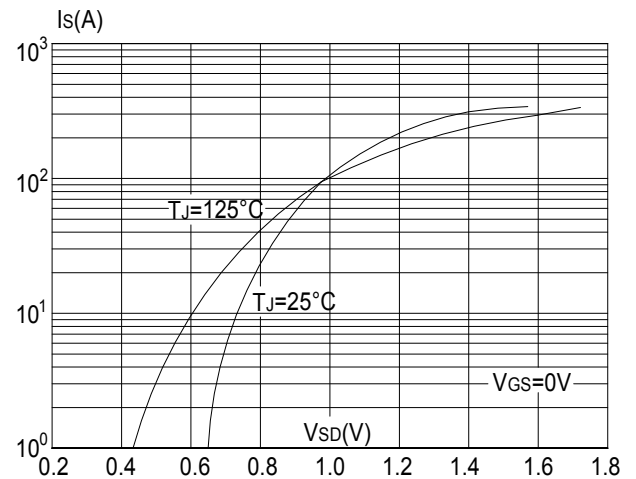


Figure 5: Gate Charge Characteristics

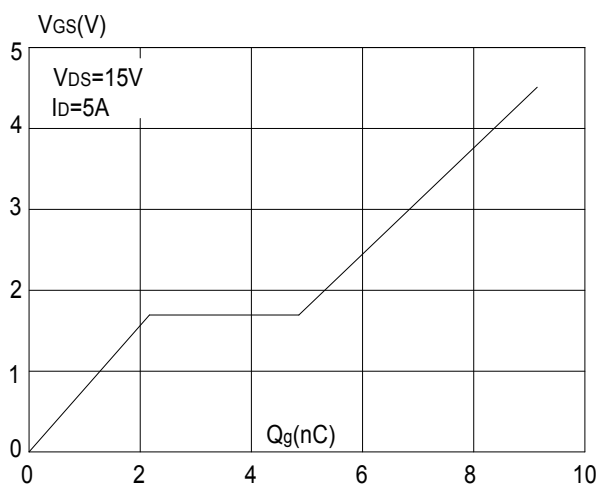


Figure 6: Capacitance Characteristics

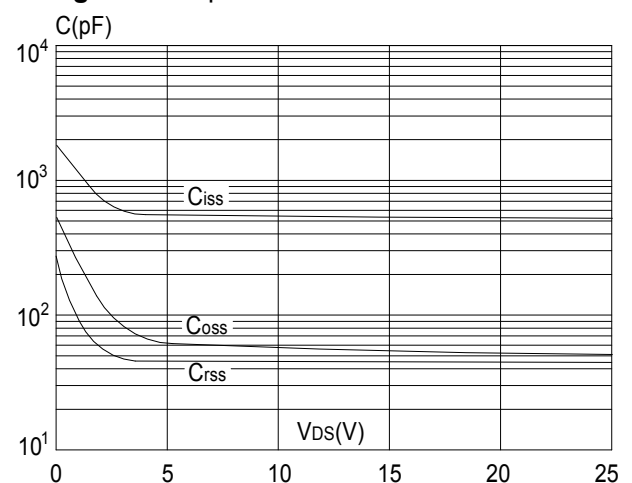




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

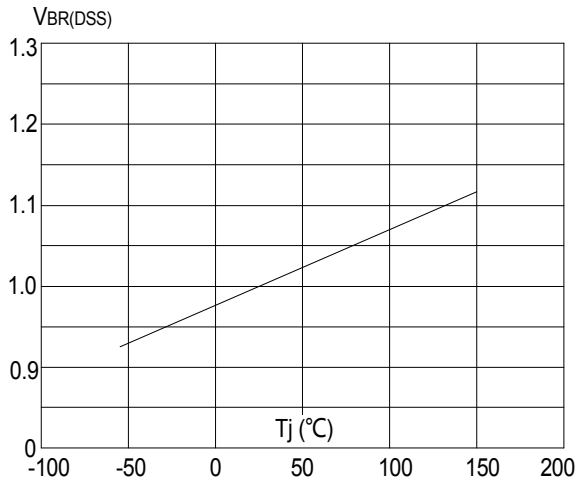


Figure 8: Normalized on Resistance vs. Junction Temperature

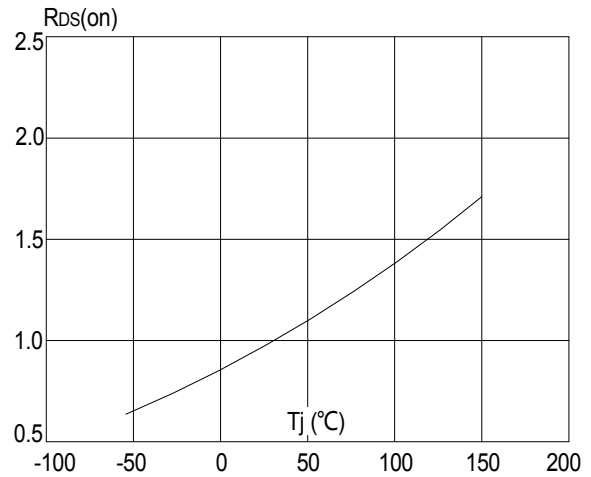


Figure 9: Maximum Safe Operating Area

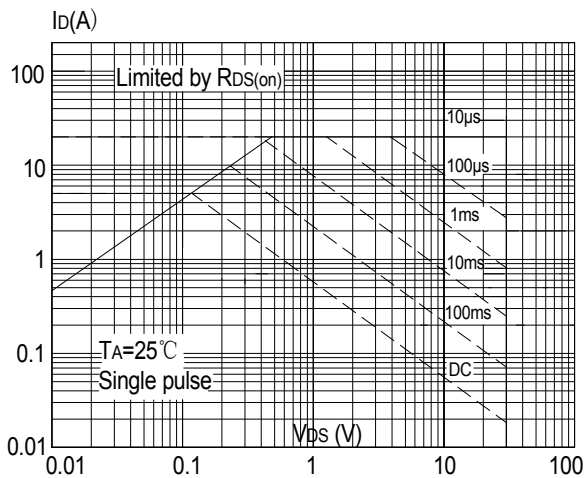


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

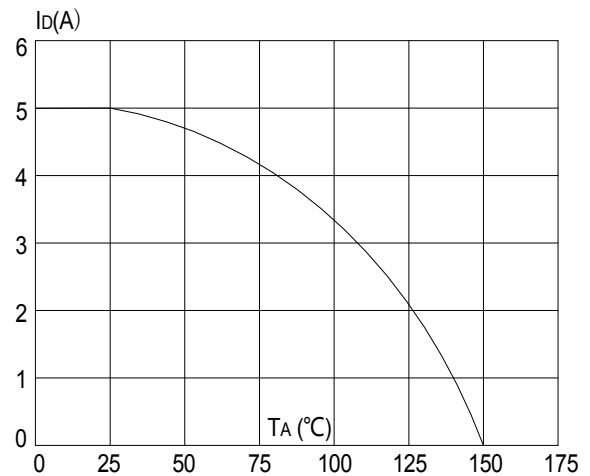
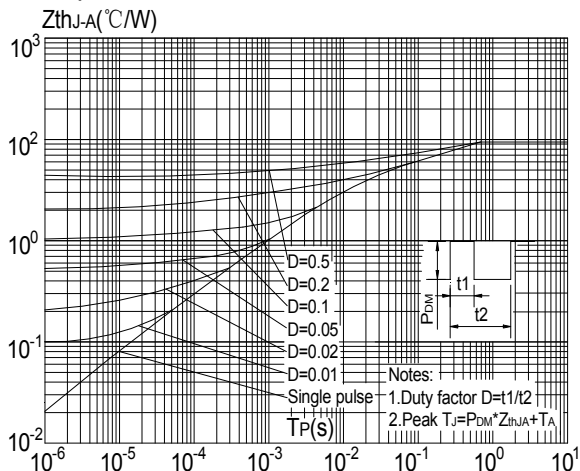
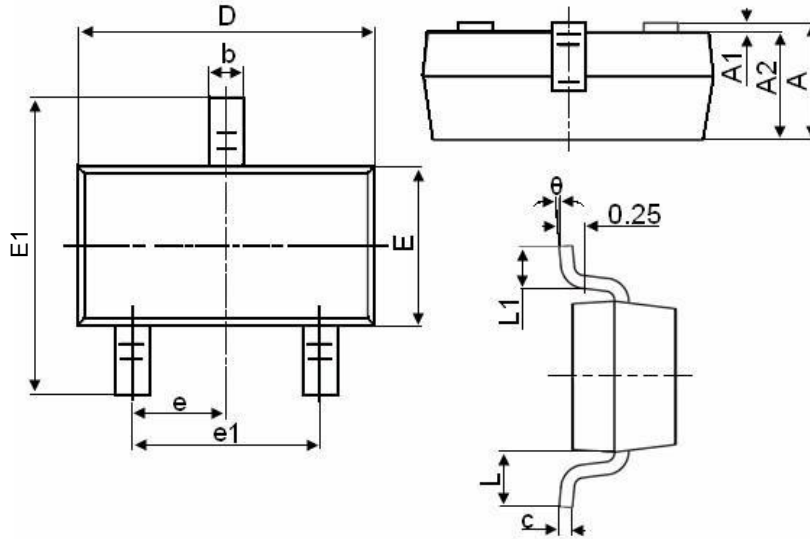


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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